Title (en)

THIN LAYER CAPACITORS WITH LARGE SCALE INTEGRATION

Title (de)

DÜNNSCHICHTKONDENSATOREN MIT HOHER INTEGRATIONSDICHTE

Title (fr)

CONDENSATEURS À COUCHE MINCE PRÉSENTANT UNE DENSITÉ D'INTÉGRATION ÉLEVÉE

Publication

EP 2926384 A1 20151007 (DE)

Application

EP 14702496 A 20140127

Priority

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- EP 2014051478 W 20140127

Abstract (en)

[origin: WO2014124796A1] The present invention relates to a two-ply, dielectric layer for a thin-layer capacitor, characterized in that a) the bottom, first ply (4) comprises a self-assembled monolayer containing phosphorus oxo compounds and b) the top, second ply (5) comprises a planarization layer containing guanidinium compounds.

IPC 8 full level

C07C 277/00 (2006.01); **C07C 279/00** (2006.01); **C07F 9/38** (2006.01); **H01B 3/18** (2006.01); **H01G 4/14** (2006.01); **H01G 4/33** (2006.01); **H01L 49/02** (2006.01); **H05K 1/16** (2006.01)

CPC (source: EP US)

C07F 9/3808 (2013.01 - EP US); **H01B 3/30** (2013.01 - EP US); **H01G 4/06** (2013.01 - EP US); **H01G 4/14** (2013.01 - EP US); **H01G 4/33** (2013.01 - EP US); **H01G 9/0032** (2013.01 - US); **H01G 9/0036** (2013.01 - US); **H01G 9/04** (2013.01 - US); **H01G 9/07** (2013.01 - US); **H01L 28/40** (2013.01 - EP US); **H05K 1/181** (2013.01 - US); H05K 1/162 (2013.01 - EP US); H05K 2201/10015 (2013.01 - US)

Citation (search report)

See references of WO 2014124796A1

Designated contracting state (EPC)

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Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

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